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## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









# TISP4072F3LM THRU TISP4082F3LM, TISP4125F3LM THRU TISP4180F3LM, TISP4240F3LM THRU TISP4380F3LM

#### BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

## TISP4xxxF3LM Overvoltage Protector Series

Ion-Implanted Breakdown Region Precise and Stable Voltage Low Voltage Overshoot under Surge

Device	V <sub>DRM</sub> V	V <sub>(BO)</sub>
'4072	58	72
'4082	66	82
'4125	100	125
'4150	120	150
'4180	145	180
'4240	180	240
'4260	200	260
'4290	220	290
'4320	240	320
'4380	270	380

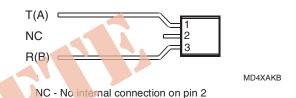
#### **Rated for International Surge Wave Shapes**

Waveshape	Standard	I <sub>TSP</sub> A		
10/160 μs	FCC Part 68	60		
0.5/700 μs	l3124	38		
10/700 μs	ITU-T K.20/21	50		
10/560 μs	FCC Part 68	45		
10/1000 μs	REA PE-60	35		

Component

# T(A) 1 2 3 MD4XAT NC - No internal connection on pin 2

#### LMF Package (LM Package with Formed Leads) (Top View)



**Device Symbol** 



Terminals T and R correspond to the alternative line designators of A and B

#### **Description**

These devices are designed to limit overvoltages on the telephone line. Overvoltages are normally caused by a.c. power system or lightning flash disturbances which are induced or conducted on to the telephone line. A single device provides 2-point protection and is typically used for the protection of 2-wire telecommunication equipment (e.g. between the Ring to Tip wires for telephones and modems). Combinations of devices can be used for multi-point protection (e.g. 3-point protection between Ring, Tip and Ground).

The protector consists of a symmetrical voltage-triggered bidirectional thyristor. Overvoltages are initially clipped by breakdown clamping until the voltage rises to the breakover level, which causes the device to crowbar into a low-voltage on state. This low-voltage on state causes the current resulting from the overvoltage to be safely diverted through the device. The high crowbar holding current helps prevent d.c. latchup as the diverted current subsides.

#### **How to Order**

Device	Package	Carrier	Order As
	Straight Lead DO-92 (LM)	Bulk Pack	TISP4xxxF3LM-S
TISP4xxxF3LM	Straight Lead DO-92 (LIVI)	Tape and Reeled TISP4xxxF3LM	
	Formed Lead DO-92 (LMF)	Tape and Reeled	TISP4xxxF3LMFR-S

Insert xxx value corresponding to protection voltages of 072, 082, 125 etc.

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#### **Description (Continued)**

This TISP4xxxF3LM range consists of ten voltage variants to meet various maximum system voltage levels (58 V to 270 V). They are guaranteed to voltage limit and withstand the listed international lightning surges in both polarities. These protection devices are supplied in a DO-92 (LM) cylindrical plastic package. The TISP4xxxF3LM is a straight lead DO-92 supplied in bulk pack and on tape and reeled. The TISP4xxxF3LMF is a formed lead DO-92 supplied only on tape and reeled.

#### Absolute Maximum Ratings, T<sub>A</sub> = 25 °C (Unless Otherwise Noted)

Rating	Symbol	Value	Unit
'4072		± 58	
'4082 '4125		± 66	
		± 100	
·4150		± 120	
Repetitive peak off-state voltage (0 °C < T <sub>.I</sub> < 70 °C)	VDDM	± 145	V
4240	DRIVIP	± 180	•
'4260		± 200	
4290		± 220	
4320		± 240	
4380		± 270	
Non-repetitive peak on-state pulse current (see Notes 1, 2 and 3)			
2/10 μs (FCC Part 68, 2/10 μs voltage wave shape) excluding '4072 - '4082		175	
8/20 μs (ANSI C62.41, 1.2/50 μs voltage wave shape) excluding '4072 - '4082		120	
10/160 μs (FCC Part 68, 10/160 μs voltage wave shape)		60	
5/200 μs (VDE 0433, 2 kV, 10/700 μs voltage wave shape)		50	
0.2/310 μs (l3124, 1.5 kV, 0.5/700 μs voltage wave shape)	I <sub>TSP</sub>	38	Α
5/310 μs (ITU-T K.20/21, 1.5 kV, 10/700 μs voltage wave shape)	'ISP	38	, , ,
5/310 μs (FTZ R12, 2 kV, 10/700 μs voltage wave shape)		50	
10/560 μs (FCC Part 68, 10/560 μs voltage wave shape)		45	
10/1000 μs (REA PE-60, 10/1000 μs voltage wave shape)		35	
2/10 μs (FCC Part 68, 2/10 μs voltage wave shape) '4072 - '4082 only		80	
8/20 μs (ANSI C62.41, 1.2/50 μs voltage wave shape) '4072 - '4082 only		70	
Non-repetitive peak on-state current (see Notes 2 and 3)		4	Α
50/60 Hz, 1 s	ITSM	4	A
Initial rate of rise of on-state current, Linear current ramp, Maximum ramp value < 38 A	di <sub>T</sub> /dt	250	A/μs
Junction temperature	TJ	-40 to +150	°C
Storage temperature range	T <sub>stg</sub>	-55 to +150	°C

NOTES: 1. Initially the TISP must be in thermal equilibrium with 0  $^{\circ}C < T_{J} < 70 \ ^{\circ}C.$ 

- 2. The surge may be repeated after the TISP returns to its initial conditions.
- 3. Above 70 °C, derate linearly to zero at 150 °C lead temperature.

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#### Electrical Characteristics, $T_A$ = 25 °C (Unless Otherwise Noted)

	Parameter	Test Conditions	Min	Тур	Max	Unit
I <sub>DRM</sub>	Repetitive peak off- state current	$V_D = \pm V_{DRM}$ , 0 °C < $T_J$ < 70 °C			±10	μΑ
		'4072 '4082			±72 ±82	
		4125			±125	
		4150			±150	
		4/180			±180	
V <sub>(BO)</sub>	Breakover voltage	$dv/dt = \pm 250 \text{ V/ms},  R_{SOURCE} = 300 \Omega$			±240	V
		4260			±260	
		4290			±290	
		4320			±320	
		'4380			±380	
		'4072			±86	
		4082			±96	
	Impulse breakover	'4125			±143	
		$dv/dt = \pm 1000 V/μs$ , $R_{SOURCE} = 50 Ω$ '4150 '4180			±168	
V					±198	v
V <sub>(BO)</sub>	voltage	di/dt < 20 A/μs '4240			±267	V
		4260			±287	
		'4290			±317	
		4320			±347	
		4380			±407	
I <sub>(BO)</sub>	Breakover current	$dv/dt = \pm 250 \text{ V/ms},  R_{SOURCE} = 300 \Omega$	±0.15		±0.6	Α
V <sub>T</sub>	On-state voltage	$T_T = \pm 5 \text{ A,t }_W = 100 \mu\text{s}$			±3	V
I <sub>H</sub>	Holding current	$I_{T} = \pm 5$ A,d i/dt = -/+30 mA/ms	±0.15			Α
dv/dt	Critical rate of rise of off-state voltage	Linear voltage ramp, Maximum ramp value < 0.85V <sub>DRM</sub>	±5			kV/μs
I <sub>D</sub>	Off-state current	$V_{D} = \pm 50 \text{ V}$			±10	μΑ
		$f = 100 \text{ kHz}, V_d = 1 \text{ Vr.m.s., V}_D = 0,$ '4072 - '4082		63	108	
	Off-state capacitance	·4125 - ·418		43	74	
_		'4240 - '4380		44	74	nE.
C <sub>off</sub>		$f = 100 \text{ kHz},  V_d = 1 \text{ Vr.m.s.}, V_D = -50 \text{ V}$ '4072 - '4082		25	40	pF
		·4125 - ·4180		15	25	
		·4240 - ·4380		11	20	

#### **Thermal Characteristics**

Parameter		Test Conditions	Min	Тур	Max	Unit
$R_{\Theta JA}$	Junction to free air thermal resistance	EIA/JESD51-3 PCB mounted in an EIA/ JESD51-2 enclosure			120	°C/W

#### **Parameter Measurement Information**

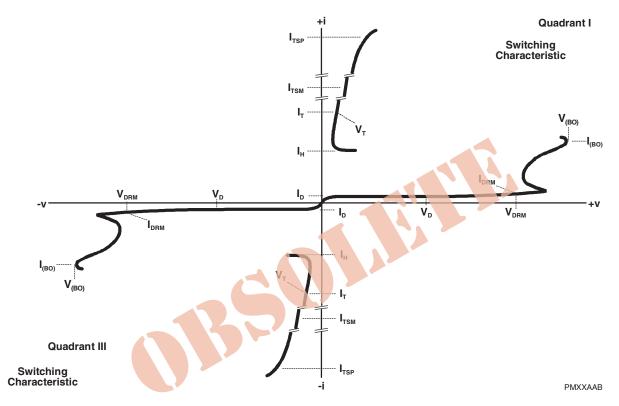
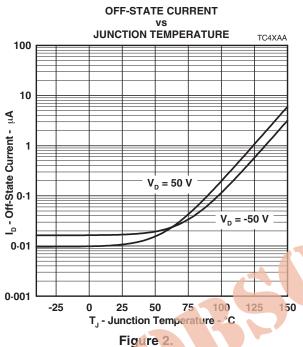


Figure 1. Voltage-Current Characteristic for R and T Terminals

All Measurements are Referenced to the T Terminal

#### **Typical Characteristics**



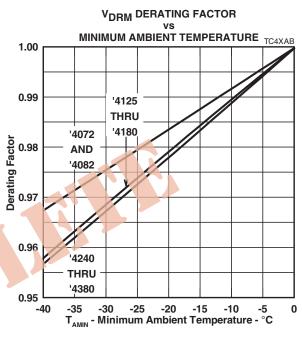
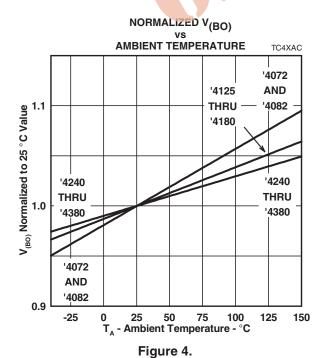
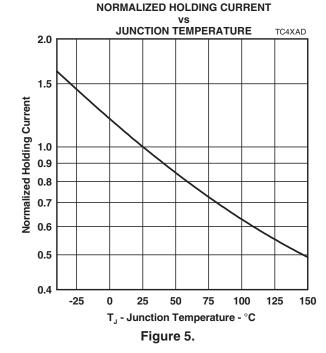


Figure 3.

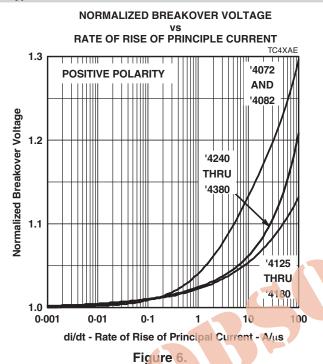




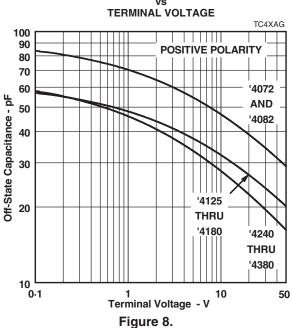
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#### **Typical Characteristics**







## NORMALIZED BREAKOVER VOLTAGE vs RATE OF RISE OF PRINCIPLE CURRENT

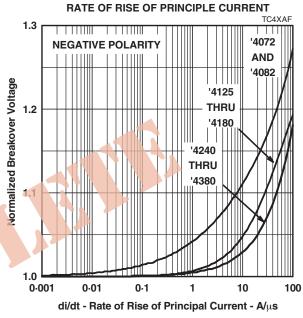
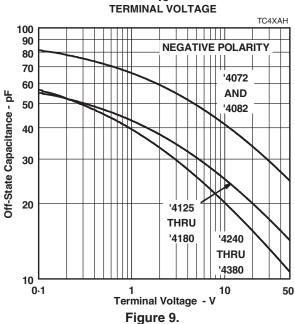


Figure 7.

## OFF-STATE CAPACITANCE vs



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#### Typical Characteristics

#### NON-REPETITIVE PEAK ON-STATE CURRENT

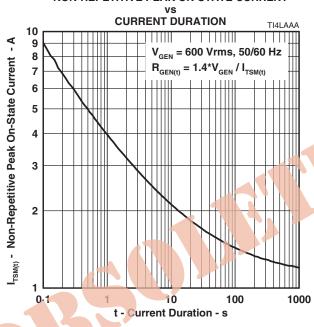


Figure 10.

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#### **MECHANICAL DATA**

#### **Device Symbolization Code**

Devices will be coded as below.

Device	Symbolization Code
TISP4072F3	4072F3
TISP4082F3	4082F3
TISP4125F3	4125F3
TISP4150F3	4150F3
TISP4180F3	4180F3
TISP4240F3	4240F3
TISP4260F3	4260F3
TISP4290F3	4290F3
TISP4320F3	4320F3
TISP4380F3	4380F3

#### **Carrier Information**

Devices are shipped in one of the carriers below. A reel contains 2,000 devices.

Device	Package	Carrier	Order As
	Straight Lead DO-92 (LM)	Bulk Pack	TISP4xxxF3LM-S
TISP4xxxF3LM	Straight Lead DO-32 (Livi)	Tape and Reeled	TISP4xxxF3LMR-S
	Formed Lead DO-92 (LMF)	Tape and Reeled	TISP4xxxF3LMFR-S

Insert xxx value corresponding to protection voltages of 072, 082, 125 etc.